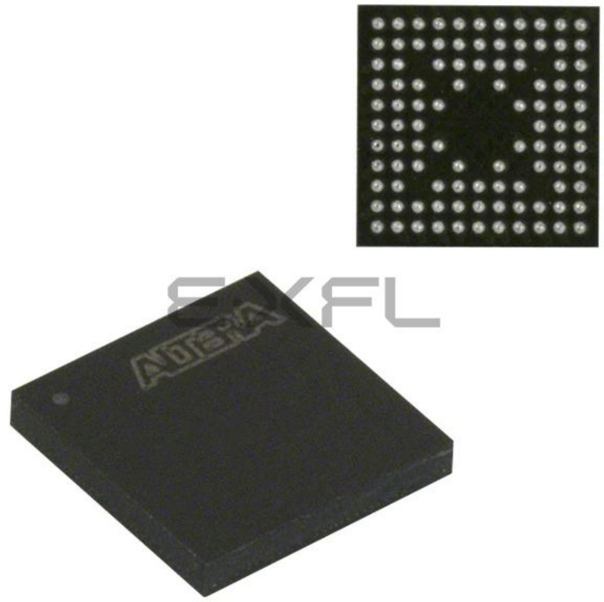
Intel - EPM570M100I5N Datasheet



Welcome to E-XFL.COM

Understanding Embedded - CPLDs (Complex Programmable Logic Devices)

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

Applications of Embedded - CPLDs

Details	
Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	5.4 ns
Voltage Supply - Internal	2.5V, 3.3V
Number of Logic Elements/Blocks	570
Number of Macrocells	440
Number of Gates	-
Number of I/O	76
Operating Temperature	-40°C ~ 100°C (TJ)
Mounting Type	Surface Mount
Package / Case	100-TFBGA
Supplier Device Package	100-MBGA (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epm570m100i5n

MAX II devices have an internal linear voltage regulator which supports external supply voltages of 3.3 V or 2.5 V, regulating the supply down to the internal operating voltage of 1.8 V. MAX IIG and MAX IIZ devices only accept 1.8 V as the external supply voltage. MAX IIZ devices are pin-compatible with MAX IIG devices in the 100-pin Micro FineLine BGA and 256-pin Micro FineLine BGA packages. Except for external supply voltage requirements, MAX II and MAX II G devices have identical pin-outs and timing specifications. Table 1–5 shows the external supply voltages supported by the MAX II family.

Table 1–5. MAX II External Supply Voltages

Devices	**EPM240** **EPM570** **EPM1270** **EPM2210**	**EPM240G** **EPM570G** **EPM1270G** **EPM2210G** **EPM240Z** **EPM570Z** *(1)*
MultiVolt core external supply voltage (V_{CCINT}) *(2)*	3.3 V, 2.5 V	1.8 V
MultiVolt I/O interface voltage levels (V_{CCIO})	1.5 V, 1.8 V, 2.5 V, 3.3 V	1.5 V, 1.8 V, 2.5 V, 3.3 V

Notes to Table 1–5:

(1) MAX IIG and MAX IIZ devices only accept 1.8 V on their `VCCINT` pins. The 1.8-V V_{CCINT} external supply powers the device core directly.

(2) MAX II devices operate internally at 1.8 V.

Referenced Documents

This chapter references the following documents:

- *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*
- *MAX II Logic Element to Macrocell Conversion Methodology* white paper

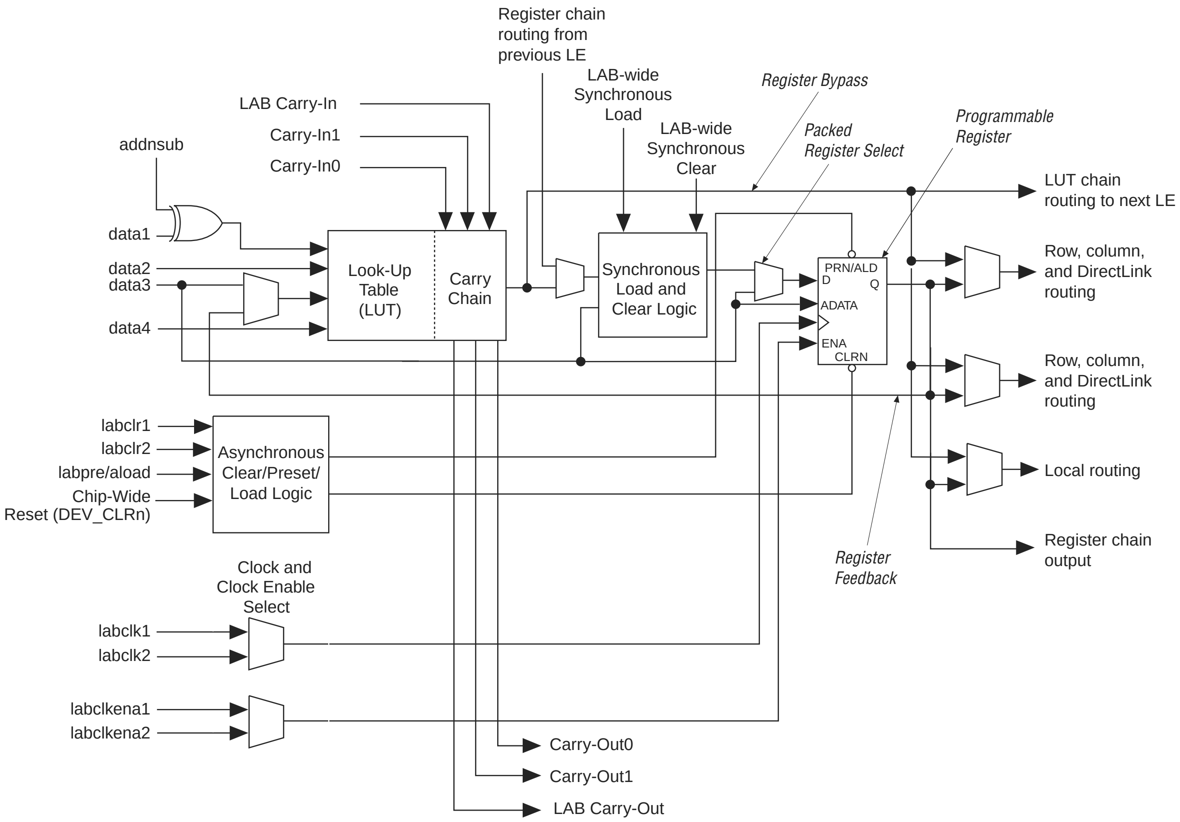
Document Revision History

Table 1–6 shows the revision history for this chapter.

Table 1–6. Document Revision History

Date and Revision	Changes Made	Summary of Changes
August 2009, version 1.9	■ Updated Table 1–2.	Added information for speed grade –8
October 2008, version 1.8	■ Updated “Introduction” section. ■ Updated new Document Format.	—
December 2007, version1.7	■ Updated Table 1–1 through Table 1–5. ■ Added “Referenced Documents” section.	Updated document with MAX IIZ information.
December 2006, version 1.6	■ Added document revision history.	—
August 2006, version 1.5	■ Minor update to features list.	—
July 2006, version 1.4	■ Minor updates to tables.	—

Figure 2–6. MAX II LE



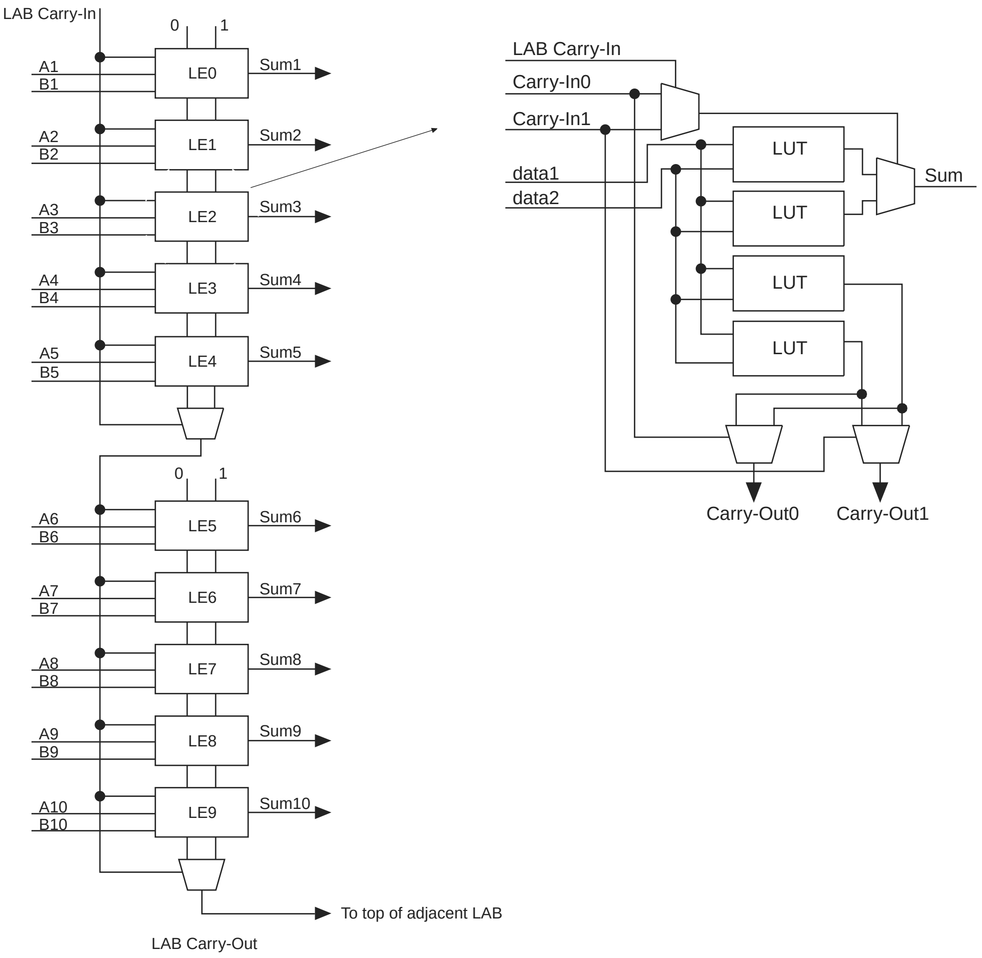
Each LE's programmable register can be configured for D, T, JK, or SR operation. Each register has data, true asynchronous load data, clock, clock enable, clear, and asynchronous load/preset inputs. Global signals, general-purpose I/O pins, or any LE can drive the register's clock and clear control signals. Either general-purpose I/O pins or LEs can drive the clock enable, preset, asynchronous load, and asynchronous data. The asynchronous load data input comes from the data3 input of the LE. For combinational functions, the LUT output bypasses the register and drives directly to the LE outputs.

Each LE has three outputs that drive the local, row, and column routing resources. The LUT or register output can drive these three outputs independently. Two LE outputs drive column or row and DirectLink routing connections and one drives local interconnect resources. This allows the LUT to drive one output while the register drives another output. This register packing feature improves device utilization because the device can use the register and the LUT for unrelated functions. Another special packing mode allows the register output to feed back into the LUT of the same LE so that the register is packed with its own fan-out LUT. This provides another mechanism for improved fitting. The LE can also drive out registered and unregistered versions of the LUT output.

The speed advantage of the carry-select chain is in the parallel precomputation of carry chains. Since the LAB carry-in selects the precomputed carry chain, not every LE is in the critical path. Only the propagation delays between LAB carry-in generation (LE 5 and LE 10) are now part of the critical path. This feature allows the MAX II architecture to implement high-speed counters, adders, multipliers, parity functions, and comparators of arbitrary width.

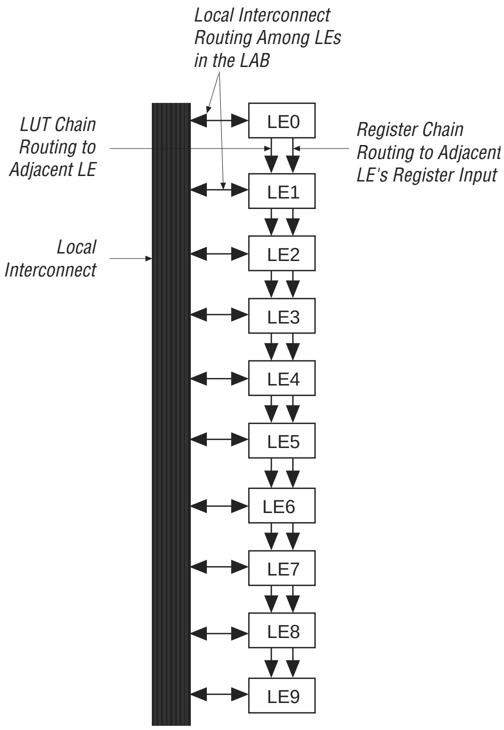
Figure 2–9 shows the carry-select circuitry in an LAB for a 10-bit full adder. One portion of the LUT generates the sum of two bits using the input signals and the appropriate carry-in bit; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for accumulator functions. Another portion of the LUT generates carry-out bits. An LAB-wide carry-in bit selects which chain is used for the addition of given inputs. The carry-in signal for each chain, `carry-in0` or `carry-in1`, selects the carry-out to carry forward to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it is fed to local, row, or column interconnects.

Figure 2–9. Carry-Select Chain



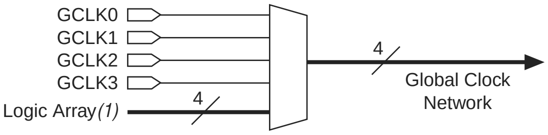
functions from LE 1 to LE 10 in the same LAB. The register chain connection allows the register output of one LE to connect directly to the register input of the next LE in the LAB for fast shift registers. The Quartus II Compiler automatically takes advantage of these resources to improve utilization and performance. Figure 2–11 shows the LUT chain and register chain interconnects.

Figure 2–11. LUT Chain and Register Chain Interconnects



The C4 interconnects span four LABs up or down from a source LAB. Every LAB has its own set of C4 interconnects to drive either up or down. Figure 2–12 shows the C4 interconnect connections from an LAB in a column. The C4 interconnects can drive and be driven by column and row IOEs. For LAB interconnection, a primary LAB or its vertical LAB neighbor can drive a given C4 interconnect. C4 interconnects can drive each other to extend their range as well as drive row interconnects for column-to-column connections.

Figure 2–13. Global Clock Generation

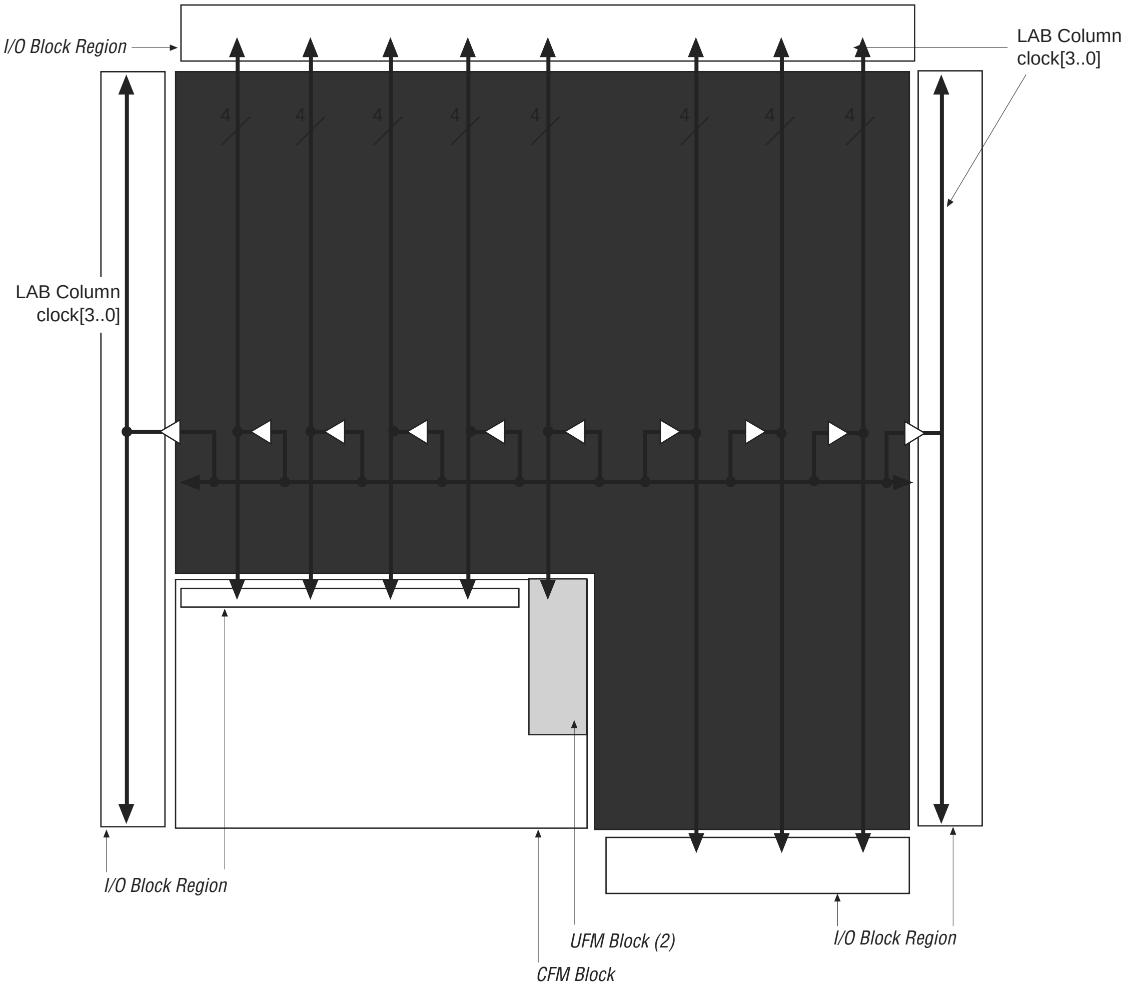


Note to Figure 2–13:

(1) Any I/O pin can use a MultiTrack interconnect to route as a logic array-generated global clock signal.

The global clock network drives to individual LAB column signals, LAB column clocks [3..0], that span an entire LAB column from the top to the bottom of the device. Unused global clocks or control signals in a LAB column are turned off at the LAB column clock buffers shown in Figure 2–14. The LAB column clocks [3..0] are multiplexed down to two LAB clock signals and one LAB clear signal. Other control signal types route from the global clock network into the LAB local interconnect. See "LAB Control Signals" on page 2–5 for more information.

Figure 2–14. Global Clock Network *(Note 1)*



Notes to Figure 2–14:

(1) LAB column clocks in I/O block regions provide high fan-out output enable signals.

(2) LAB column clocks drive to the UFM block.

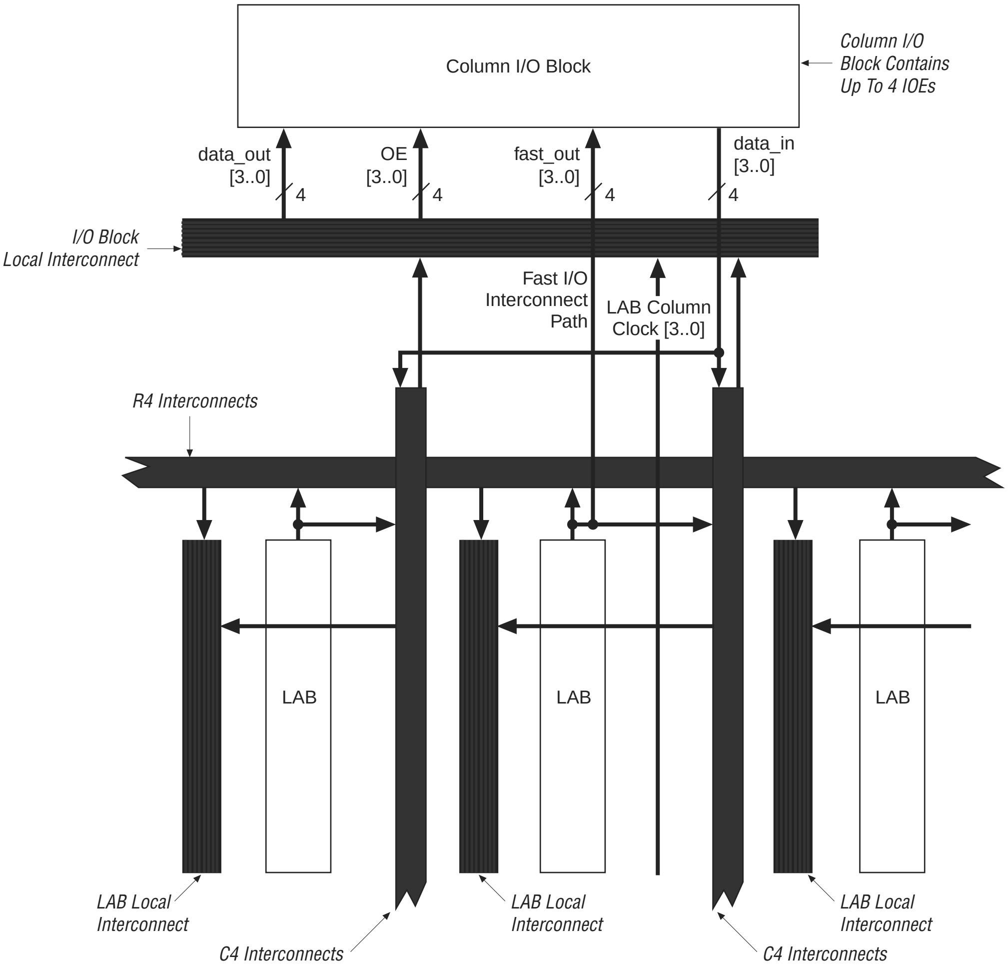
User Flash Memory Block

MAX II devices feature a single UFM block, which can be used like a serial EEPROM for storing non-volatile information up to 8,192 bits. The UFM block connects to the logic array through the MultiTrack interconnect, allowing any LE to interface to the UFM block. Figure 2–15 shows the UFM block and interface signals. The logic array is used to create customer interface or protocol logic to interface the UFM block data outside of the device. The UFM block offers the following features:

- Non-volatile storage up to 16-bit wide and 8,192 total bits
- Two sectors for partitioned sector erase
- Built-in internal oscillator that optionally drives logic array
- Program, erase, and busy signals

Figure 2–21 shows how a column I/O block connects to the logic array.

Figure 2–21. Column I/O Block Connection to the Interconnect *(Note 1)*



Note to Figure 2–21:

(1) Each of the four IOEs in the column I/O block can have one `data_out` or `fast_out` output, one `OE` output, and one `data_in` input.

I/O Standards and Banks

MAX II device IOEs support the following I/O standards:

- 3.3-V LVTTL/LVCMOS
- 2.5-V LVTTL/LVCMOS
- 1.8-V LVTTL/LVCMOS
- 1.5-V LVCMOS
- 3.3-V PCI

Table 3–3. 32-Bit MAX II Device IDCODE (Part 2 of 2)

Device	Binary IDCODE (32 Bits) *(1)*				HEX IDCODE
	Version (4 Bits)	**Part Number**	**Manufacturer Identity (11 Bits)**	**LSB (1 Bit)** *(2)*	
EPM240Z	`0000`	`0010 0000 1010 0101`	`000 0110 1110`	1	0x020A50DD
EPM570Z	`0000`	`0010 0000 1010 0110`	`000 0110 1110`	1	0x020A60DD

Notes to Table 3–2:

(1) The most significant bit (MSB) is on the left.

(2) The `IDCODE`'s least significant bit (LSB) is always 1.

For JTAG AC characteristics, refer to the *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*.

For more information about JTAG BST, refer to the *IEEE 1149.1 (JTAG) Boundary-Scan Testing for MAX II Devices* chapter in the *MAX II Device Handbook*.

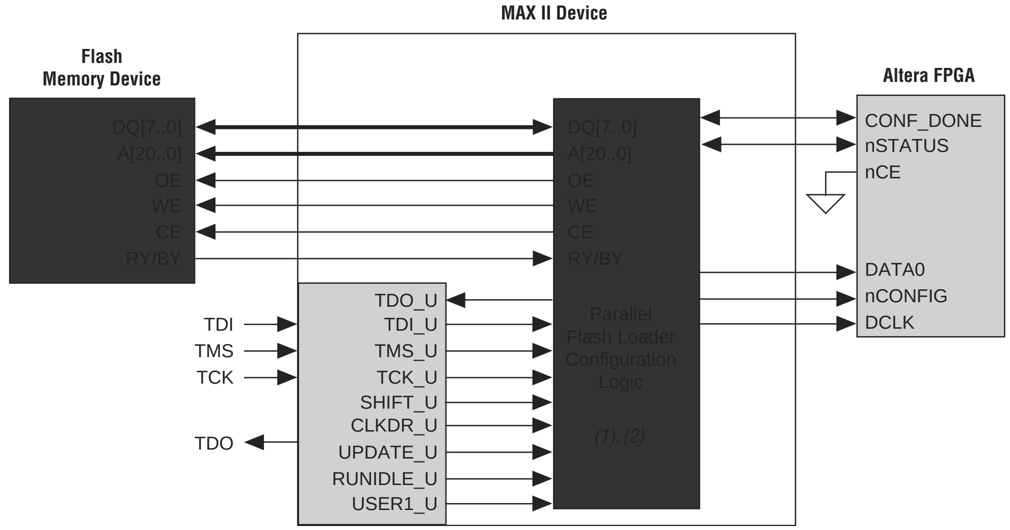
JTAG Block

The MAX II JTAG block feature allows you to access the JTAG TAP and state signals when either the `USER0` or `USER1` instruction is issued to the JTAG TAP. The `USER0` and `USER1` instructions bring the JTAG boundary-scan chain (`TDI`) through the user logic instead of the MAX II device's boundary-scan cells. Each `USER` instruction allows for one unique user-defined JTAG chain into the logic array.

Parallel Flash Loader

The JTAG block ability to interface JTAG to non-JTAG devices is ideal for general-purpose flash memory devices (such as Intel- or Fujitsu-based devices) that require programming during in-circuit test. The flash memory devices can be used for FPGA configuration or be part of system memory. In many cases, the MAX II device is already connected to these devices as the configuration control logic between the FPGA and the flash device. Unlike ISP-capable CPLD devices, bulk flash devices do not have JTAG TAP pins or connections. For small flash devices, it is common to use the serial JTAG scan chain of a connected device to program the non-JTAG flash device. This is slow and inefficient in most cases and impractical for large parallel flash devices. Using the MAX II device's JTAG block as a parallel flash loader, with the Quartus II software, to program and verify flash contents provides a fast and cost-effective means of in-circuit programming during test. Figure 3–1 shows MAX II being used as a parallel flash loader.

Figure 3–1. MAX II Parallel Flash Loader



Notes to Figure 3–1:

(1) This block is implemented in LEs.

(2) This function is supported in the Quartus II software.

In System Programmability

MAX II devices can be programmed in-system via the industry standard 4-pin IEEE Std. 1149.1 (JTAG) interface. In-system programmability (ISP) offers quick, efficient iterations during design development and debugging cycles. The logic, circuitry, and interconnects in the MAX II architecture are configured with flash-based SRAM configuration elements. These SRAM elements require configuration data to be loaded each time the device is powered. The process of loading the SRAM data is called configuration. The on-chip configuration flash memory (CFM) block stores the SRAM element's configuration data. The CFM block stores the design's configuration pattern in a reprogrammable flash array. During ISP, the MAX II JTAG and ISP circuitry programs the design pattern into the CFM block's non-volatile flash array.

The MAX II JTAG and ISP controller internally generate the high programming voltages required to program the CFM cells, allowing in-system programming with any of the recommended operating external voltage supplies (that is, 3.3 V/2.5 V or 1.8 V for the MAX IIG and MAX IIZ devices). ISP can be performed anytime after V_{CCINT} and all V_{CCIO} banks have been fully powered and the device has completed the configuration power-up time. By default, during in-system programming, the I/O pins are tri-stated and weakly pulled-up to V_{CCIO} to eliminate board conflicts. The in-system programming clamp and real-time ISP feature allow user control of I/O state or behavior during ISP.

For more information, refer to "In-System Programming Clamp" on page 3–6 and "Real-Time ISP" on page 3–7.

These devices also offer an `ISP_DONE` bit that provides safe operation when in-system programming is interrupted. This `ISP_DONE` bit, which is the last bit programmed, prevents all I/O pins from driving until the bit is programmed.

Table 3–4 shows the programming times for MAX II devices using in-circuit testers to execute the algorithm vectors in hardware. Software-based programming tools used with download cables are slightly slower because of data processing and transfer limitations.

Table 3–4. MAX II Device Family Programming Times

Description	EPM240 EPM240G EPM240Z	EPM570 EPM570G EPM570Z	EPM1270 EPM1270G	EPM2210 EPM2210G	Unit
Erase + Program (1 MHz)	1.72	2.16	2.90	3.92	sec
Erase + Program (10 MHz)	1.65	1.99	2.58	3.40	sec
Verify (1 MHz)	0.09	0.17	0.30	0.49	sec
Verify (10 MHz)	0.01	0.02	0.03	0.05	sec
Complete Program Cycle (1 MHz)	1.81	2.33	3.20	4.41	sec
Complete Program Cycle (10 MHz)	1.66	2.01	2.61	3.45	sec

UFM Programming

The Quartus II software, with the use of POF, Jam, or JBC files, supports programming of the user flash memory (UFM) block independent of the logic array design pattern stored in the CFM block. This allows updating or reading UFM contents through ISP without altering the current logic array design, or vice versa. By default, these programming files and methods will program the entire flash memory contents, which includes the CFM block and UFM contents. The stand-alone embedded Jam STAPL player and Jam Byte-Code Player provides action commands for programming or reading the entire flash memory (UFM and CFM together) or each independently.

For more information, refer to the *Using Jam STAPL for ISP via an Embedded Processor* chapter in the *MAX II Device Handbook*.

In-System Programming Clamp

By default, the IEEE 1532 instruction used for entering ISP automatically tri-states all I/O pins with weak pull-up resistors for the duration of the ISP sequence. However, some systems may require certain pins on MAX II devices to maintain a specific DC logic level during an in-field update. For these systems, an optional in-system programming clamp instruction exists in MAX II circuitry to control I/O behavior during the ISP sequence. The in-system programming clamp instruction enables the device to sample and sustain the value on an output pin (an input pin would remain tri-stated if sampled) or to explicitly set a logic high, logic low, or tri-state value on any pin. Setting these options is controlled on an individual pin basis using the Quartus II software.

For more information, refer to the *Real-Time ISP and ISP Clamp for MAX II Devices* chapter in the *MAX II Device Handbook*.

Real-Time ISP

For systems that require more than DC logic level control of I/O pins, the real-time ISP feature allows you to update the CFM block with a new design image while the current design continues to operate in the SRAM logic array and I/O pins. A new programming file is updated into the MAX II device without halting the original design's operation, saving down-time costs for remote or field upgrades. The updated CFM block configures the new design into the SRAM upon the next power cycle. It is also possible to execute an immediate configuration of the SRAM without a power cycle by using a specific sequence of ISP commands. The configuration of SRAM without a power cycle takes a specific amount of time (t_{CONFIG}). During this time, the I/O pins are tri-stated and weakly pulled-up to V_{CCIO}.

Design Security

All MAX II devices contain a programmable security bit that controls access to the data programmed into the CFM block. When this bit is programmed, design programming information, stored in the CFM block, cannot be copied or retrieved. This feature provides a high level of design security because programmed data within flash memory cells is invisible. The security bit that controls this function, as well as all other programmed data, is reset only when the device is erased. The SRAM is also invisible and cannot be accessed regardless of the security bit setting. The UFM block data is not protected by the security bit and is accessible through JTAG or logic array connections.

Programming with External Hardware

MAX II devices can be programmed by downloading the information via in-circuit testers, embedded processors, the Altera® ByteblasterMV™, MasterBlaster™, ByteBlaster™ II, and USB-Blaster cables.

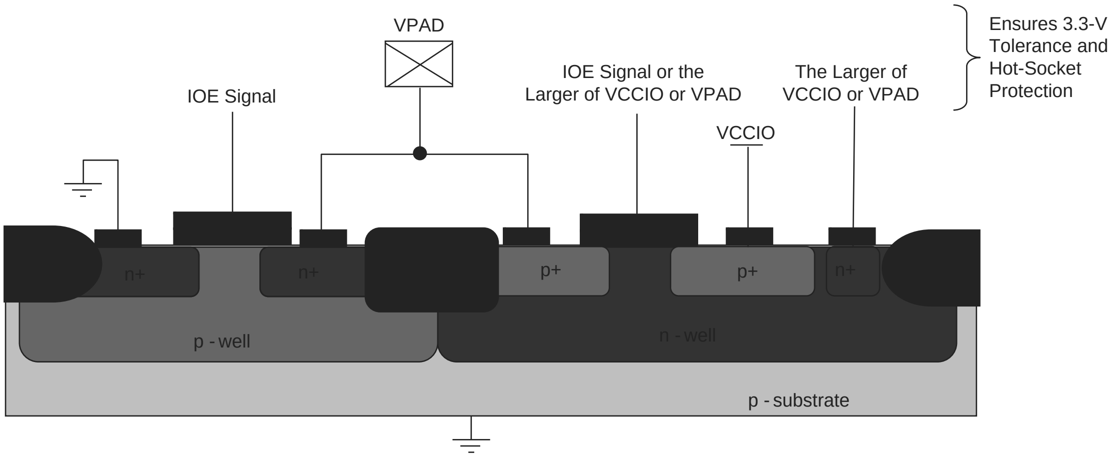
BP Microsystems, System General, and other programming hardware manufacturers provide programming support for Altera devices. Check their websites for device support information.

Referenced Documents

This chapter references the following documents:

- *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*
- *IEEE 1149.1 (JTAG) Boundary-Scan Testing for MAX II Devices* chapter in the *MAX II Device Handbook*
- *Real-Time ISP and ISP Clamp for MAX II Devices* chapter in the *MAX II Device Handbook*
- *Using Jam STAPL for ISP via an Embedded Processor* chapter in the *MAX II Device Handbook*

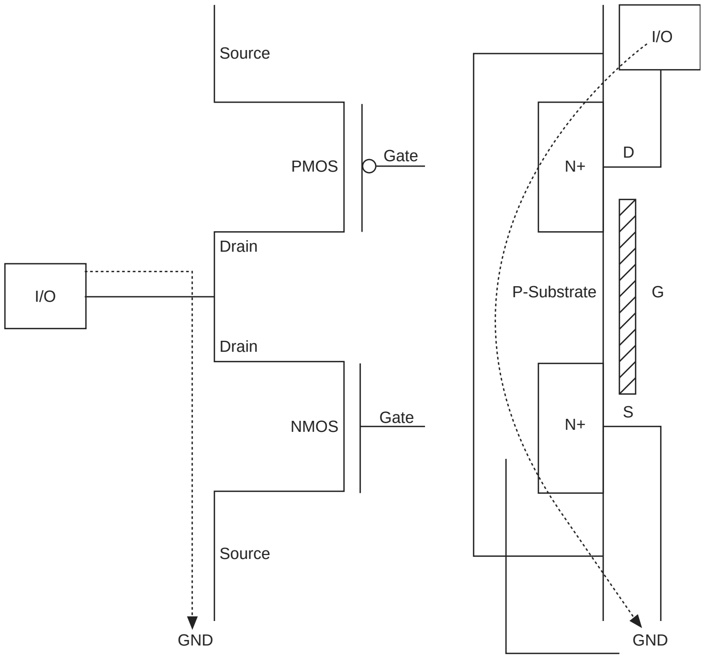
Figure 4–2. Transistor-Level Diagram of MAX II Device I/O Buffers



The CMOS output drivers in the I/O pins intrinsically provide electrostatic discharge (ESD) protection. There are two cases to consider for ESD voltage strikes: positive voltage zap and negative voltage zap.

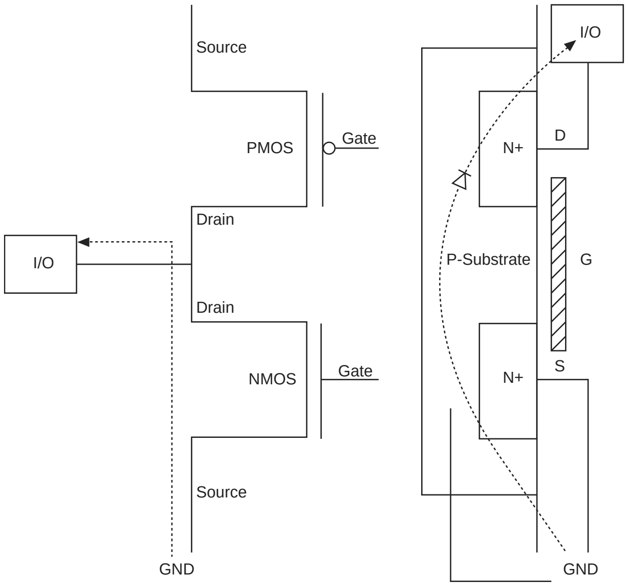
A positive ESD voltage zap occurs when a positive voltage is present on an I/O pin due to an ESD charge event. This can cause the N+ (Drain)/ P-Substrate junction of the N-channel drain to break down and the N+ (Drain)/P-Substrate/N+ (Source) intrinsic bipolar transistor turn on to discharge ESD current from I/O pin to GND. The dashed line (see Figure 4–3) shows the ESD current discharge path during a positive ESD zap.

Figure 4–3. ESD Protection During Positive Voltage Zap



When the I/O pin receives a negative ESD zap at the pin that is less than –0.7 V (0.7 V is the voltage drop across a diode), the intrinsic
P-Substrate/N+ drain diode is forward biased. Therefore, the discharge ESD current path is from GND to the I/O pin, as shown in Figure 4–4.

Figure 4–4. ESD Protection During Negative Voltage Zap



Power-On Reset Circuitry

MAX II devices have POR circuits to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up. The POR circuit monitors these voltages, triggering download from the non-volatile configuration flash memory (CFM) block to the SRAM logic, maintaining tri-state of the I/O pins (with weak pull-up resistors enabled) before and during this process. When the MAX II device enters user mode, the POR circuit releases the I/O pins to user functionality. The POR circuit of the MAX II (except MAX IIZ) device continues to monitor the V_{CCINT} voltage level to detect a brown-out condition. The POR circuit of the MAX IIZ device does not monitor the V_{CCINT} voltage level after the device enters into user mode. More details are provided in the following sub-sections.

Power-Up Timing

Table 5–12 shows the power-up timing characteristics for MAX II devices.

Table 5–12. MAX II Power-Up Timing

Symbol	Parameter	Device	Min	Typ	Max	Unit
t_{CONFIG} *(1)*	The amount of time from when minimum V_{CCINT} is reached until the device enters user mode *(2)*	EPM240	—	—	200	µs
		EPM570	—	—	300	µs
		EPM1270	—	—	300	µs
		EPM2210	—	—	450	µs

Notes to Table 5–12:

(1) Table 5–12 values apply to commercial and industrial range devices. For extended temperature range devices, the t_{CONFIG} maximum values are as follows:

Device	Maximum
EPM240	300 µs
EPM570	400 µs
EPM1270	400 µs
EPM2210	500 µs

(2) For more information about POR trigger voltage, refer to the *Hot Socketing and Power-On Reset in MAX II Devices* chapter in the *MAX II Device Handbook*.

Power Consumption

Designers can use the Altera® PowerPlay Early Power Estimator and PowerPlay Power Analyzer to estimate the device power.

For more information about these power analysis tools, refer to the *Understanding and Evaluating Power in MAX II Devices* chapter in the *MAX II Device Handbook* and the *PowerPlay Power Analysis* chapter in volume 3 of the *Quartus II Handbook.*

Timing Model and Specifications

MAX II devices timing can be analyzed with the Altera Quartus® II software, a variety of popular industry-standard EDA simulators and timing analyzers, or with the timing model shown in Figure 5–2.

MAX II devices have predictable internal delays that enable the designer to determine the worst-case timing of any design. The software provides timing simulation, point-to-point delay prediction, and detailed timing analysis for device-wide performance evaluation.

Table 5–17. t_{ZX} IOE Microparameter Adders for Fast Slew Rate (Part 2 of 2)

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
1.5-V LVCMOS	4 mA	—	1,118	—	1,454	—	1,789	—	580	—	588	—	588	ps
	2 mA	—	2,410	—	3,133	—	3,856	—	915	—	923	—	923	ps
3.3-V PCI	20 mA	—	19	—	25	—	31	—	72	—	71	—	74	ps

Table 5–18. t_{ZX} IOE Microparameter Adders for Slow Slew Rate

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	6,350	—	6,050	—	5,749	—	5,951	—	5,952	—	6,063	ps
	8 mA	—	9,383	—	9,083	—	8,782	—	6,534	—	6,533	—	6,662	ps
3.3-V LVCMOS	8 mA	—	6,350	—	6,050	—	5,749	—	5,951	—	5,952	—	6,063	ps
	4 mA	—	9,383	—	9,083	—	8,782	—	6,534	—	6,533	—	6,662	ps
2.5-V LVTTL / LVCMOS	14 mA	—	10,412	—	10,112	—	9,811	—	9,110	—	9,105	—	9,237	ps
	7 mA	—	13,613	—	13,313	—	13,012	—	9,830	—	9,835	—	9,977	ps
3.3-V PCI	20 mA	—	–75	—	–97	—	–120	—	6,534	—	6,533	—	6,662	ps

Table 5–19. t_{XZ} IOE Microparameter Adders for Fast Slew Rate

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	8 mA	—	–56	—	–72	—	–89	—	–69	—	–69	—	–69	ps
3.3-V LVCMOS	8 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	4 mA	—	–56	—	–72	—	–89	—	–69	—	–69	—	–69	ps
2.5-V LVTTL / LVCMOS	14 mA	—	–3	—	–4	—	–5	—	–7	—	–11	—	–11	ps
	7 mA	—	–47	—	–61	—	–75	—	–66	—	–70	—	–70	ps
1.8-V LVTTL / LVCMOS	6 mA	—	119	—	155	—	191	—	45	—	34	—	37	ps
	3 mA	—	207	—	269	—	331	—	34	—	22	—	25	ps
1.5-V LVCMOS	4 mA	—	606	—	788	—	970	—	166	—	154	—	155	ps
	2 mA	—	673	—	875	—	1,077	—	190	—	177	—	179	ps
3.3-V PCI	20 mA	—	71	—	93	—	114	—	–69	—	–69	—	–69	ps

Table 5–21. UFM Block Internal Timing Microparameters (Part 2 of 3)

		MAX II / MAX IIG						MAX IIZ						
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
Symbol	**Parameter**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Unit**
t_{DDS}	Data register data in setup to data register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{DDH}	Data register data in hold from data register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{DP}	Program signal to data clock hold time	0	—	0	—	0	—	0	—	0	—	0	—	ns
t_{PB}	Maximum delay between program rising edge to UFM busy signal rising edge	—	960	—	960	—	960	—	960	—	960	—	960	ns
t_{BP}	Minimum delay allowed from UFM busy signal going low to program signal going low	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{PPMX}	Maximum length of busy pulse during a program	—	100	—	100	—	100	—	100	—	100	—	100	µs
t_{AE}	Minimum erase signal to address clock hold time	0	—	0	—	0	—	0	—	0	—	0	—	ns
t_{EB}	Maximum delay between the erase rising edge to the UFM busy signal rising edge	—	960	—	960	—	960	—	960	—	960	—	960	ns
t_{BE}	Minimum delay allowed from the UFM busy signal going low to erase signal going low	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{EPMX}	Maximum length of busy pulse during an erase	—	500	—	500	—	500	—	500	—	500	—	500	ms
t_{DCO}	Delay from data register clock to data register output	—	5	—	5	—	5	—	5	—	5	—	5	ns

Table 5–23. EPM240 Global Clock External I/O Timing Parameters (Part 2 of 2)

			MAX II / MAX IIG						MAX IIZ						
			–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
Symbol	**Parameter**	**Condition**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Unit**
f_{CNT}	Maximum global clock frequency for 16-bit counter	—	—	304.0 *(1)*	—	247.5	—	201.1	—	184.1	—	123.5	—	118.3	MHz

Note to Table 5–23:

(1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

Table 5–24 shows the external I/O timing parameters for EPM570 devices.

Table 5–24. EPM570 Global Clock External I/O Timing Parameters (Part 1 of 2)

			MAX II / MAX IIG						MAX IIZ						
			–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
Symbol	**Parameter**	**Condition**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Unit**
t_{PD1}	Worst case pin-to-pin delay through 1 look-up table (LUT)	10 pF	—	5.4	—	7.0	—	8.7	—	9.5	—	15.1	—	17.7	ns
t_{PD2}	Best case pin-to-pin delay through 1 LUT	10 pF	—	3.7	—	4.8	—	5.9	—	5.7	—	7.7	—	8.5	ns
t_{SU}	Global clock setup time	—	1.2	—	1.5	—	1.9	—	2.2	—	3.9	—	4.4	—	ns
t_{H}	Global clock hold time	—	0	—	0	—	0	—	0	—	0	—	0	—	ns
t_{CO}	Global clock to output delay	10 pF	2.0	4.5	2.0	5.8	2.0	7.1	2.0	6.7	2.0	8.2	2.0	8.7	ns
t_{CH}	Global clock high time	—	166	—	216	—	266	—	253	—	335	—	339	—	ps
t_{CL}	Global clock low time	—	166	—	216	—	266	—	253	—	335	—	339	—	ps
t_{CNT}	Minimum global clock period for 16-bit counter	—	3.3	—	4.0	—	5.0	—	5.4	—	8.1	—	8.4	—	ns

Table 5–26 shows the external I/O timing parameters for EPM2210 devices.

Table 5–26. EPM2210 Global Clock External I/O Timing Parameters

Symbol	Parameter	Condition	MAX II / MAX IIG						Unit
			–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		
			Min	Max	Min	Max	Min	Max	
t_{PD1}	Worst case pin-to-pin delay through 1 look-up table (LUT)	10 pF	—	7.0	—	9.1	—	11.2	ns
t_{PD2}	Best case pin-to-pin delay through 1 LUT	10 pF	—	3.7	—	4.8	—	5.9	ns
t_{SU}	Global clock setup time	—	1.2	—	1.5	—	1.9	—	ns
t_H	Global clock hold time	—	0	—	0	—	0	—	ns
t_{CO}	Global clock to output delay	10 pF	2.0	4.6	2.0	6.0	2.0	7.4	ns
t_{CH}	Global clock high time	—	166	—	216	—	266	—	ps
t_{CL}	Global clock low time	—	166	—	216	—	266	—	ps
t_{CNT}	Minimum global clock period for 16-bit counter	—	3.3	—	4.0	—	5.0	—	ns
f_{CNT}	Maximum global clock frequency for 16-bit counter	—	—	304.0 *(1)*	—	247.5	—	201.1	MHz

Note to Table 5–26:

(1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

External Timing I/O Delay Adders

The I/O delay timing parameters for I/O standard input and output adders, and input delays are specified by speed grade independent of device density.

Table 5–27 through Table 5–31 show the adder delays associated with I/O pins for all packages. The delay numbers for –3, –4, and –5 speed grades shown in Table 5–27 through Table 5–33 are based on an EPM1270 device target, while –6, –7, and –8 speed grade values are based on an EPM570Z device target. If an I/O standard other than 3.3-V LVTTL is selected, add the input delay adder to the external t_{SU} timing parameters shown in Table 5–23 through Table 5–26. If an I/O standard other than 3.3-V LVTTL with 16 mA drive strength and fast slew rate is selected, add the output delay adder to the external t_{CO} and t_{PD} shown in Table 5–23 through Table 5–26.

Table 5–27. External Timing Input Delay Adders (Part 1 of 2)

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	Without Schmitt Trigger	—	0	—	0	—	0	—	0	—	0	—	0	ps
	With Schmitt Trigger	—	334	—	434	—	535	—	387	—	434	—	442	ps

Table 5–27. External Timing Input Delay Adders (Part 2 of 2)

I/O Standard		**MAX II / MAX IIG**						**MAX IIZ**						**Unit**
		–3 Speed Grade		**–4 Speed Grade**		**–5 Speed Grade**		**–6 Speed Grade**		**–7 Speed Grade**		**–8 Speed Grade**		
		Min	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	
3.3-V LVCMOS	Without Schmitt Trigger	—	0	—	0	—	0	—	0	—	0	—	0	ps
	With Schmitt Trigger	—	334	—	434	—	535	—	387	—	434	—	442	ps
2.5-V LVTTL / LVCMOS	Without Schmitt Trigger	—	23	—	30	—	37	—	42	—	43	—	43	ps
	With Schmitt Trigger	—	339	—	441	—	543	—	429	—	476	—	483	ps
1.8-V LVTTL / LVCMOS	Without Schmitt Trigger	—	291	—	378	—	466	—	378	—	373	—	373	ps
1.5-V LVCMOS	Without Schmitt Trigger	—	681	—	885	—	1,090	—	681	—	622	—	658	ps
3.3-V PCI	Without Schmitt Trigger	—	0	—	0	—	0	—	0	—	0	—	0	ps

Table 5–28. External Timing Input Delay t_{GLOB} Adders for GCLK Pins

I/O Standard		**MAX II / MAX IIG**						**MAX IIZ**						**Unit**
		–3 Speed Grade		**–4 Speed Grade**		**–5 Speed Grade**		**–6 Speed Grade**		**–7 Speed Grade**		**–8 Speed Grade**		
		Min	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	
3.3-V LVTTL	Without Schmitt Trigger	—	0	—	0	—	0	—	0	—	0	—	0	ps
	With Schmitt Trigger	—	308	—	400	—	493	—	387	—	434	—	442	ps
3.3-V LVCMOS	Without Schmitt Trigger	—	0	—	0	—	0	—	0	—	0	—	0	ps
	With Schmitt Trigger	—	308	—	400	—	493	—	387	—	434	—	442	ps
2.5-V LVTTL / LVCMOS	Without Schmitt Trigger	—	21	—	27	—	33	—	42	—	43	—	43	ps
	With Schmitt Trigger	—	423	—	550	—	677	—	429	—	476	—	483	ps
1.8-V LVTTL / LVCMOS	Without Schmitt Trigger	—	353	—	459	—	565	—	378	—	373	—	373	ps
1.5-V LVCMOS	Without Schmitt Trigger	—	855	—	1,111	—	1,368	—	681	—	622	—	658	ps
3.3-V PCI	Without Schmitt Trigger	—	6	—	7	—	9	—	0	—	0	—	0	ps

Table 5–29. External Timing Output Delay and t_{OD} Adders for Fast Slew Rate

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	8 mA	—	65	—	84	—	104	—	–6	—	–2	—	–3	ps
3.3-V LVCMOS	8 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	4 mA	—	65	—	84	—	104	—	–6	—	–2	—	–3	ps
2.5-V LVTTL / LVCMOS	14 mA	—	122	—	158	—	195	—	–63	—	–71	—	–88	ps
	7 mA	—	193	—	251	—	309	—	10	—	–1	—	1	ps
1.8-V LVTTL / LVCMOS	6 mA	—	568	—	738	—	909	—	128	—	118	—	118	ps
	3 mA	—	654	—	850	—	1,046	—	352	—	327	—	332	ps
1.5-V LVCMOS	4 mA	—	1,059	—	1,376	—	1,694	—	421	—	400	—	400	ps
	2 mA	—	1,167	—	1,517	—	1,867	—	757	—	743	—	743	ps
3.3-V PCI	20 mA	—	3	—	4	—	5	—	–6	—	–2	—	–3	ps

Table 5–30. External Timing Output Delay and t_{OD} Adders for Slow Slew Rate

I/O Standard		MAX II / MAX IIG						MAX IIZ						Unit
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTL	16 mA	—	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	8 mA	—	7,946	—	7,627	—	7,308	—	6,541	—	6,570	—	6,720	ps
3.3-V LVCMOS	8 mA	—	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	4 mA	—	7,946	—	7,627	—	7,308	—	6,541	—	6,570	—	6,720	ps
2.5-V LVTTL / LVCMOS	14 mA	—	10,434	—	10,115	—	9,796	—	9,141	—	9,154	—	9,297	ps
	7 mA	—	11,548	—	11,229	—	10,910	—	9,861	—	9,874	—	10,037	ps
1.8-V LVTTL / LVCMOS	6 mA	—	22,927	—	22,608	—	22,289	—	21,811	—	21,854	—	21,857	ps
	3 mA	—	24,731	—	24,412	—	24,093	—	23,081	—	23,034	—	23,107	ps
1.5-V LVCMOS	4 mA	—	38,723	—	38,404	—	38,085	—	39,121	—	39,124	—	39,124	ps
	2 mA	—	41,330	—	41,011	—	40,692	—	40,631	—	40,634	—	40,634	ps
3.3-V PCI	20 mA	—	261	—	339	—	418	—	6,644	—	6,627	—	6,914	ps